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## MR27V6452D

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4,194,304-Word x 16-Bit or 8,388,608-Word x 8-Bit

8-Word x 16-Bit or 16-Word x 8-Bit Page Mode

Production Programmed Read Only Memory (P2ROM)

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### DESCRIPTION

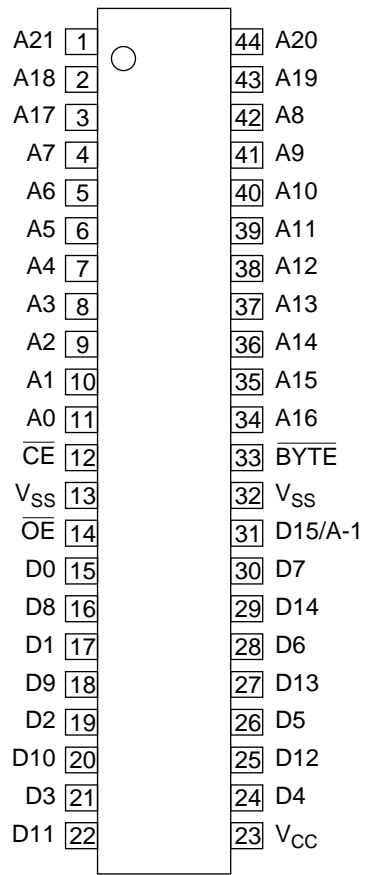
The MR27V6452D is a 64Mbit Production Programmed Read-Only Memory (P2ROM) with page mode. Its configuration can be electrically switched between 4,194,304 word x 16bit and 8,388,608 word x 8bit. The MR27V6452D operates on a single +3.3V power supply and is TTL compatible. The MR27V6452D provides Page mode which can greatly reduce the read access time. Since the MR27V6452D operates asynchronously, external clocks are not required, making this device easy-to-use. The MR27V6452D is suitable as large-capacity fixed memory for microcomputers and data terminals. It is manufactured using a CMOS double silicon gate technology and is offered in 44-pin SOP package.

### FEATURES

- 4,194,304 word x 16bit / 8,388,608 word x 8bit electrically switchable configuration
- Single +3.3V power supply
- Access time 120ns
  - Page mode access time 30ns
- Input / Output TTL compatible
- Three-state output
- Package

44-pin plastic SOP (SOP44-P-600-1.27-K) (Product name : MR27V6452D-xxMA)

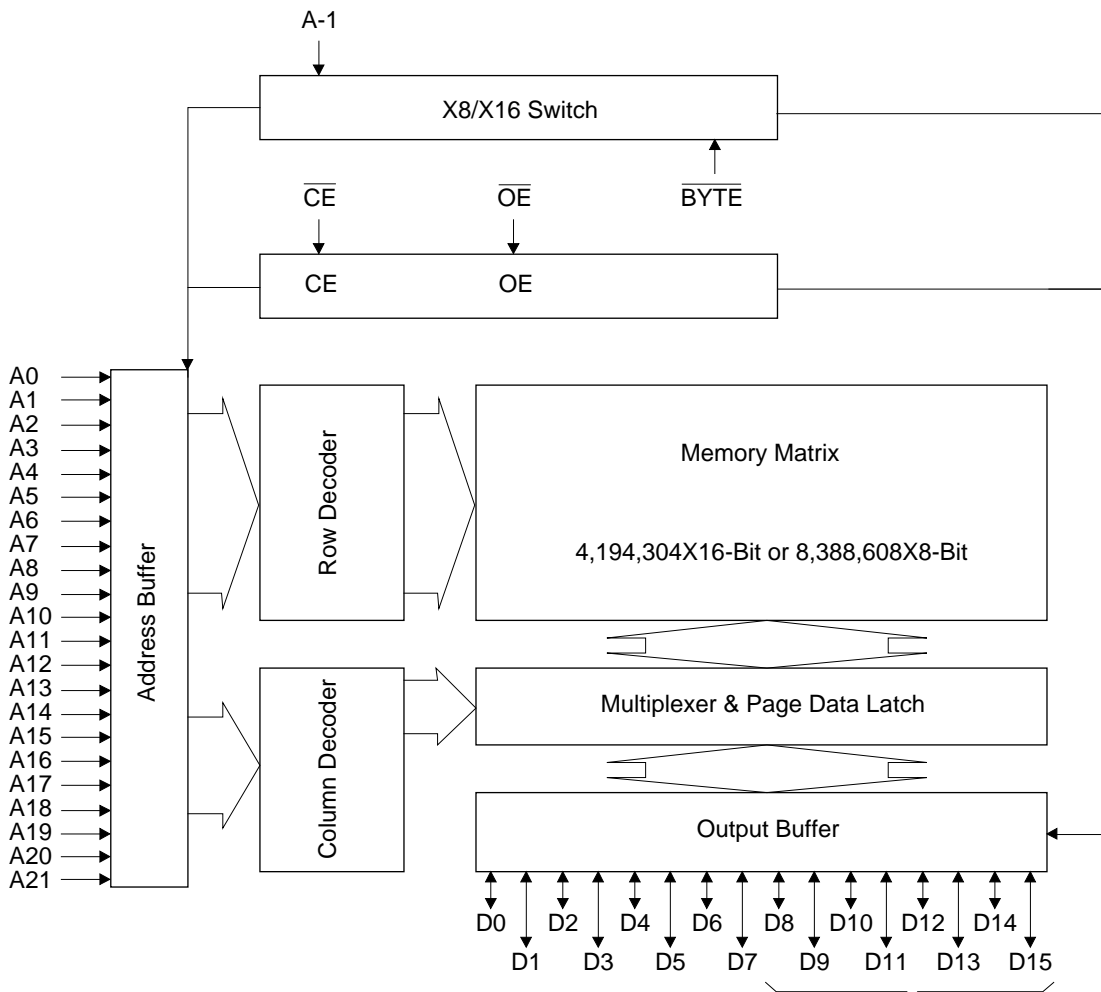
## PIN CONFIGURATION (TOP VIEW)



44-pin SOP

PIN NAMES	FUNCTIONS
D15/A-1	Data output / Address input
A0-A21	Address input
D0-D14	Data output
$\overline{CE}$	Chip enable
$\overline{OE}$	Output enable
$V_{CC}$	Power supply voltage
$V_{SS}$	GND
$\overline{BYTE}$	Mode switch

## BLOCK DIAGRAM



In 8-bit output mode, these pins are three-stated and pin D15 functions as the A-1 address pin.

## FUNCTION TABLE

MODE	$\overline{\text{CE}}$	$\overline{\text{OE}}$	$\overline{\text{BYTE}}$	$V_{\text{CC}}$	D0 - D7	D8 - D14	D15/A-1
READ (16-Bit)	L	L	H	3.3V	$D_{\text{OUT}}$		
READ (8-Bit)	L	L	L		$D_{\text{OUT}}$	Hi-Z	L/H
OUTPUT DISABLE	L	H	H		Hi-Z		*
			L		Hi-Z		*
STAND-BY	H	*	H	Hi-Z		*	
			L	Hi-Z		*	

\* : Don't Care

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Condition	Value	Unit
Operating temperature under bias	$T_{opr}$	-	0 to 70	°C
Storage temperature	$T_{stg}$		-55 to 125	°C
Input voltage	$V_I$	relative to $V_{SS}$	-0.5 to $V_{CC} + 0.5$	V
Output voltage	$V_O$		-0.5 to $V_{CC} + 0.5$	V
Power supply voltage	$V_{CC}$		-0.5 to 5	V
Power dissipation per package	$P_D$	-	1.0	W

**RECOMMENDED OPERATING CONDITIONS FOR READ**

(Ta=0 to 70°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
$V_{CC}$ power supply voltage	$V_{CC}$	$V_{CC}=3.0V-3.6V$	3.0	-	3.6	V
Input "H" level	$V_{IH}$		2.2	-	$V_{CC}+0.5^*$	V
Input "L" level	$V_{IL}$		-0.5**	-	0.6	V

Voltage is relative to  $V_{SS}$ \* :  $V_{CC}+1.5V$  (Max.) when pulse width of overshoot is less than 10nS.

\*\* : -1.5V (Min.) when pulse width of undershoot is less than 10nS.

**ELECTRICAL CHARACTERISTICS (Read operation)****DC Characteristics**(V<sub>CC</sub>=3.3V±0.3V, T<sub>a</sub>=0 to 70°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input leakage current	I <sub>LI</sub>	V <sub>I</sub> =0 to V <sub>CC</sub>	-	-	10	μA
Output leakage current	I <sub>LO</sub>	V <sub>O</sub> =0 to V <sub>CC</sub>	-	-	10	μA
V <sub>CC</sub> power supply current (Standby)	I <sub>CS1</sub>	$\overline{CE}=V_{CC}$	-	-	50	μA
	I <sub>CS2</sub>	$\overline{CE}=V_{IH}$	-	-	1	mA
V <sub>CC</sub> power supply current (Read)	I <sub>CCA</sub>	$\overline{CE}=V_{IL}$ , $\overline{OE}=V_{IH}$ t <sub>c</sub> =120ns	-	-	100	mA
Input "H" level	V <sub>IH</sub>	-	2.2	-	V <sub>CC</sub> +0.5*	V
Input "L" level	V <sub>IL</sub>	-	-0.5**	-	0.6	V
Output "H" level	V <sub>OH</sub>	I <sub>OH</sub> =-400μA	2.4	-	-	V
Output "L" level	V <sub>OL</sub>	I <sub>OL</sub> =2.1mA	-	-	0.4	V

Voltage is relative to V<sub>SS</sub>\* : V<sub>CC</sub>+1.5V (Max.) when pulse width of overshoot is less than 10nS.

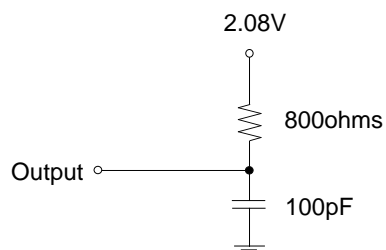
\*\* : -1.5V (Min.) when pulse width of undershoot is less than 10nS.

**AC Characteristics**(V<sub>CC</sub>=3.3V±0.3V, T<sub>a</sub>=0 to 70°C)

Parameter	Symbol	Condition	Min.	Max.	Unit
Address access cycle time	T <sub>C</sub>	-	120	-	ns
Address access time	T <sub>ACC</sub>	$\overline{CE}=\overline{OE}=V_{IL}$	-	120	ns
Page access cycle time	T <sub>PC</sub>	-	30	-	ns
Page access time	T <sub>PAC</sub>	-	-	30	ns
$\overline{CE}$ access time	T <sub>CE</sub>	$\overline{OE}=V_{IL}$	-	120	ns
$\overline{OE}$ access time	T <sub>OE</sub>	$\overline{CE}=V_{IL}$	-	40	ns
Output disable time	T <sub>CHZ</sub>	$\overline{OE}=V_{IL}$	0	30	ns
	T <sub>OHZ</sub>	$\overline{CE}=V_{IL}$	0	25	ns
Output hold time	T <sub>OH</sub>	$\overline{CE}=\overline{OE}=V_{IL}$	0	-	ns

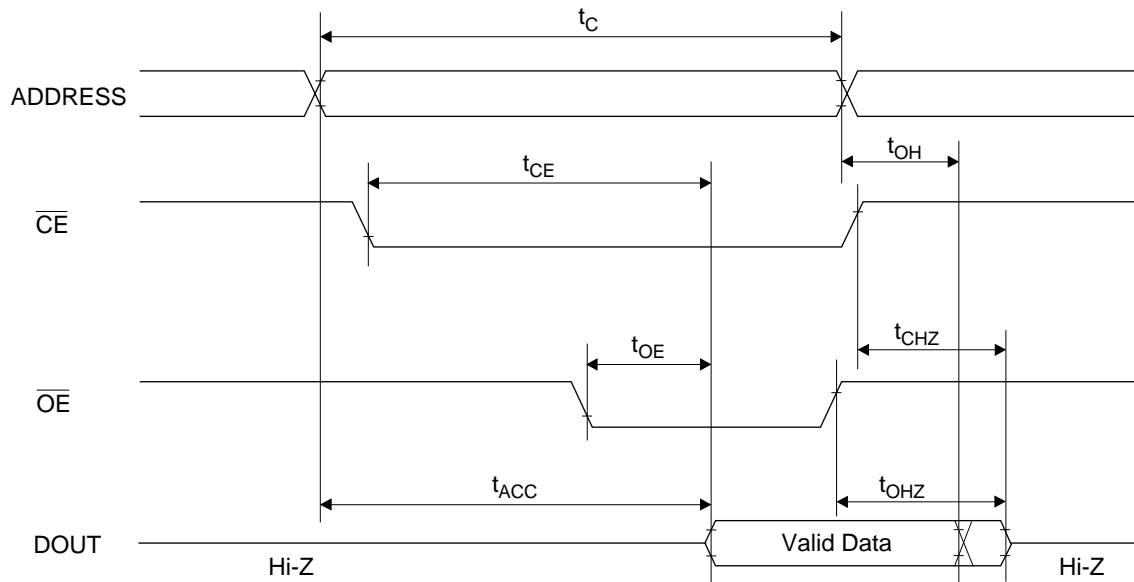
## Measurement conditions

Input signal level	-----	0V/3V
Input timing reference level	-----	0.8V/2.0V
Output load	-----	100pF
Output timing reference level	-----	0.8V/2.0V

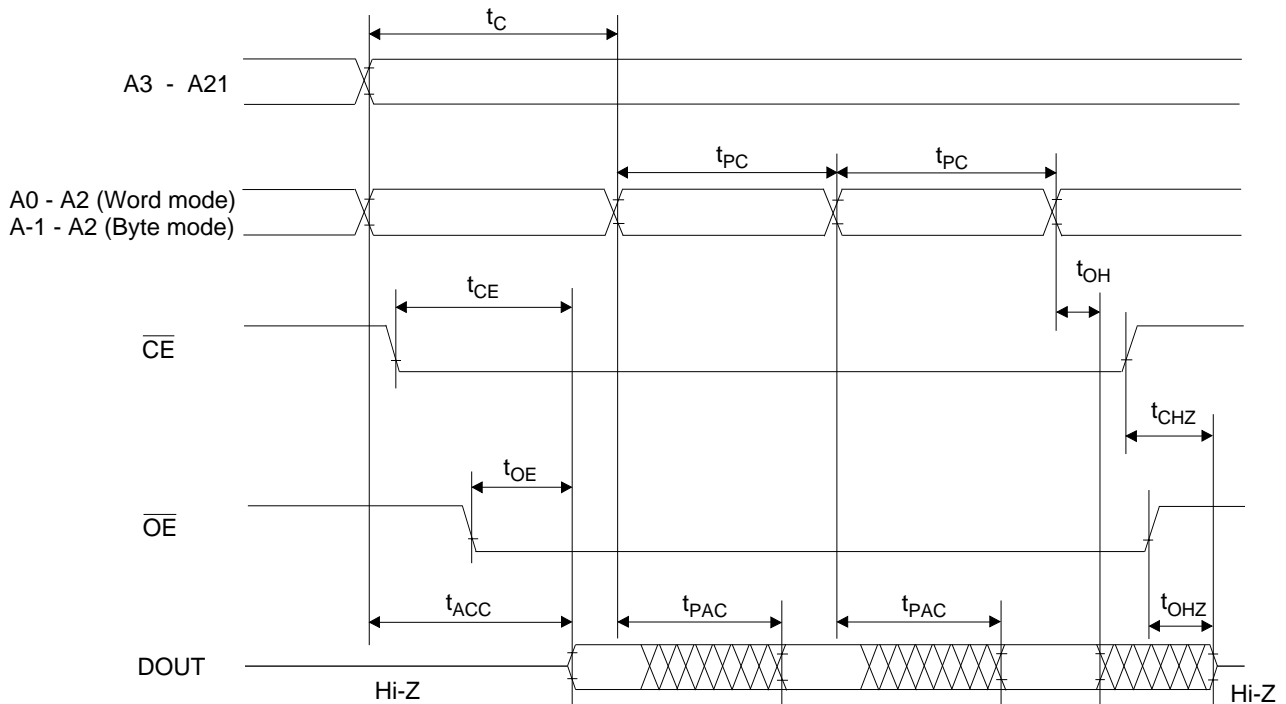


## TIMING CHART

## NORMAL MODE READ CYCLE



## PAGE MODE READ CYCLE



**PIN Capacitance** $(V_{CC}=3.3V, T_a=25^{\circ}C, f=1MHz)$ 

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input	$C_{IN1}$	$V_I=0V$	-	-	8	pF
$\overline{BYTE}$	$C_{IN2}$		-	-	120	
Output	$C_{OUT}$	$V_O=0V$	-	-	10	